

SKN 320



Stud Diode

Rectifier Diode

SKN 320

SKR 320

Features

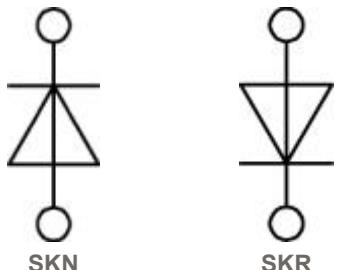
- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M24 x 1,5
- SKN: anode to stud,
SKR: cathode to stud

Typical Applications

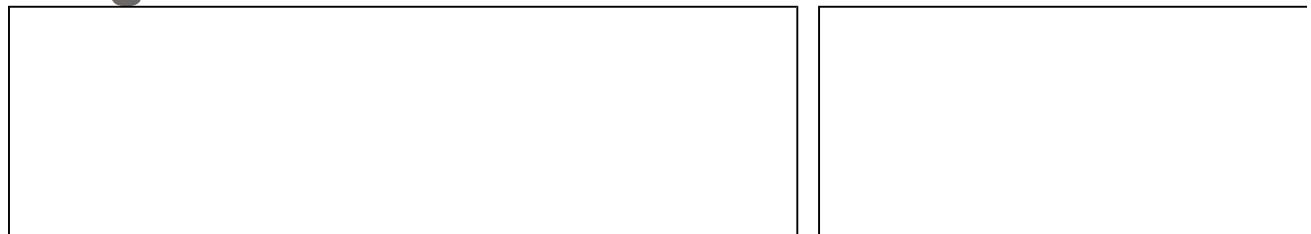
- All-purpose high power rectifier diodes
- Cooling via heatsinks
- Non-controllable and half-controllable rectifiers
- Free-wheeling diodes
- Recommended snubber network:
RC: 1 μ F, 20 Ω ($P_R = 2$ W),
 $R_p = 25$ k Ω ($P_R = 20$ W)

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 700$ A (maximum value for $I_{FAV} = 320$ A (sin. 180; T
400	400	SKN 320/04
800	800	SKR 320/04
1200	1200	SKN 320/08
1400	1400	SKR 320/08
1600	1600	SKN 320/12
		SKR 320/12
		SKN 320/14
		SKR 320/14
		SKN 320/16
		SKR 320/16

Symbol	Conditions
I_{FAV}	sin. 180; $T_c = 85$ (100) °C
I_D	P 1/200; $T_a = 45$ °C; B2 / B6
	K 0,55F; $T_a = 35$ °C; B2 / B6
I_{FSM}	$T_{vj} = 25$ °C; 10 ms
	$T_{vj} = 180$ °C; 10 ms
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms
	$T_{vj} = 180$ °C; 8,3 ... 10 ms
V_F	$T_{vj} = 25$ °C; $I_F = 1000$ A
$V_{(TO)}$	$T_{vj} = 180$ °C
r_T	$T_{vj} = 180$ °C
I_{RD}	$T_{vj} = 180$ °C; $V_{RD} = V_{RRM}$
Q_{rr}	$T_{vj} = 160$ °C; - $di_F/dt = 10$ A/ μ s
$R_{th(j-c)}$	
$R_{th(c-s)}$	
T_{vj}	
T_{stg}	
V_{isol}	
M_s	
a	to heatsink
m	approx.
Case	



Diagrams



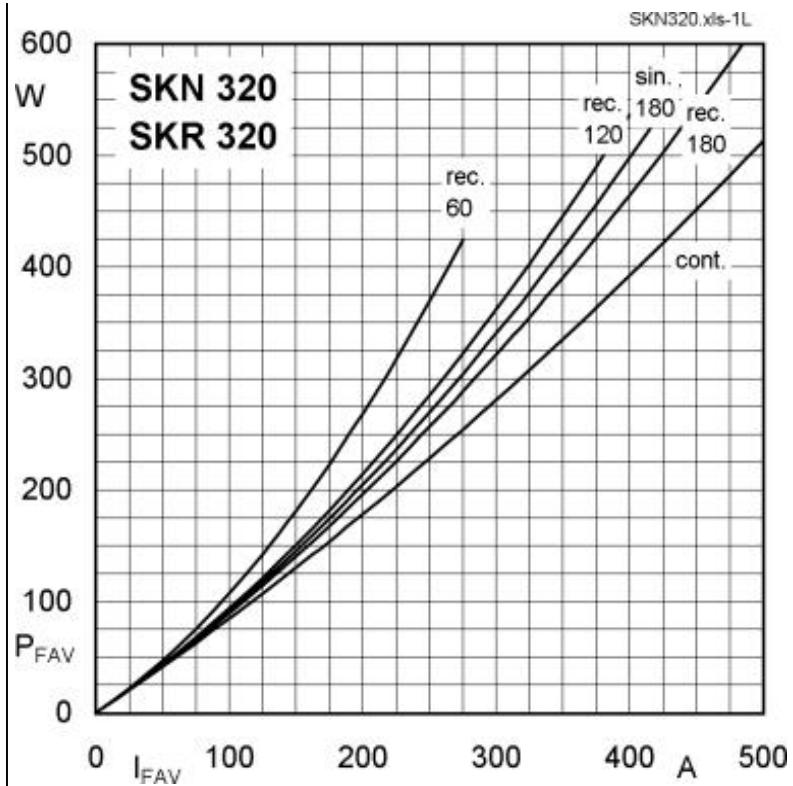


Fig. 1L Power dissipation vs. forward current

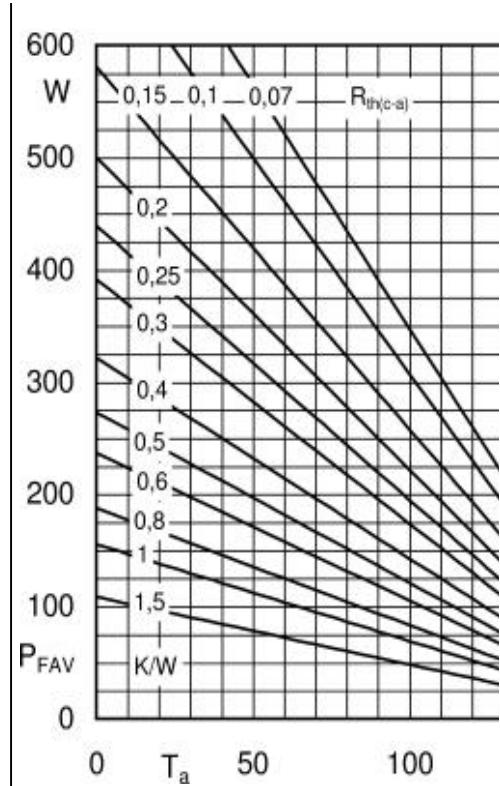


Fig. 1R Power dissipation vs. ambient temperature

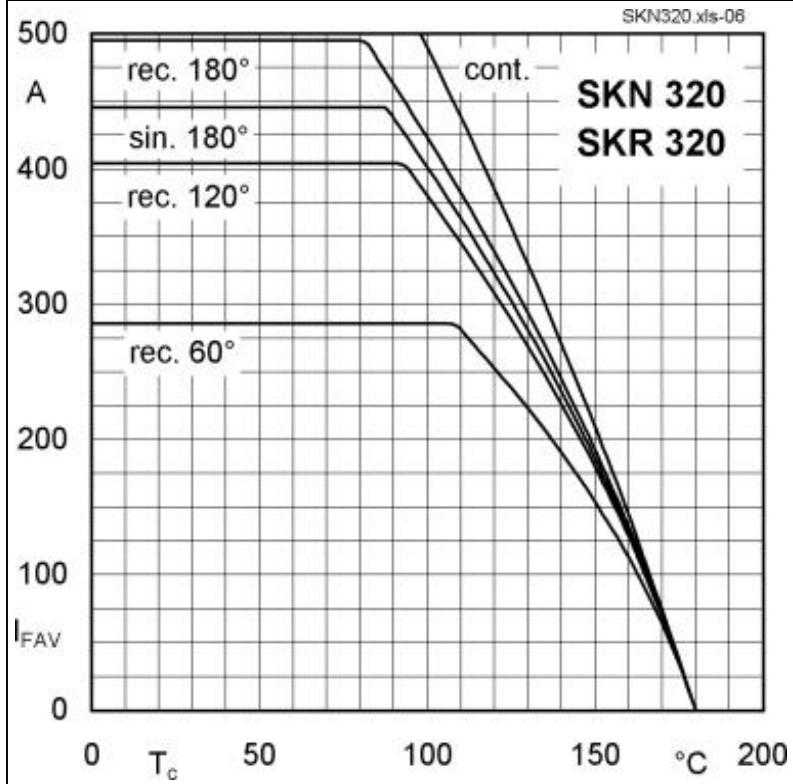


Fig. 2 Forward current vs. case temperature

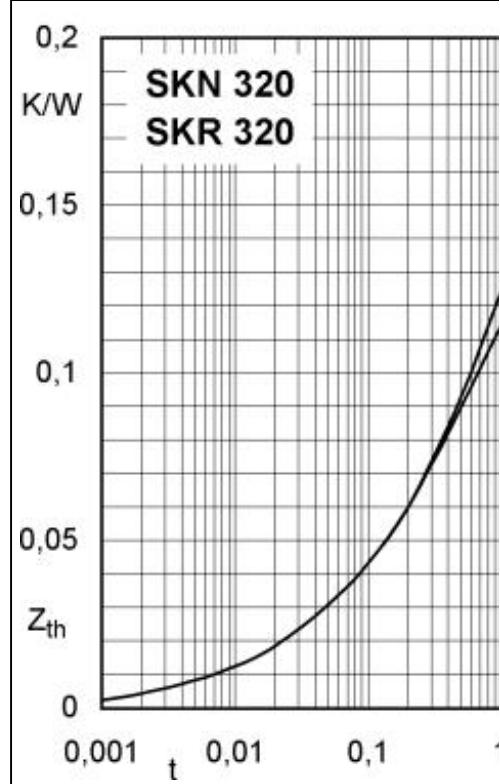


Fig. 4 Transient thermal impedance vs. time

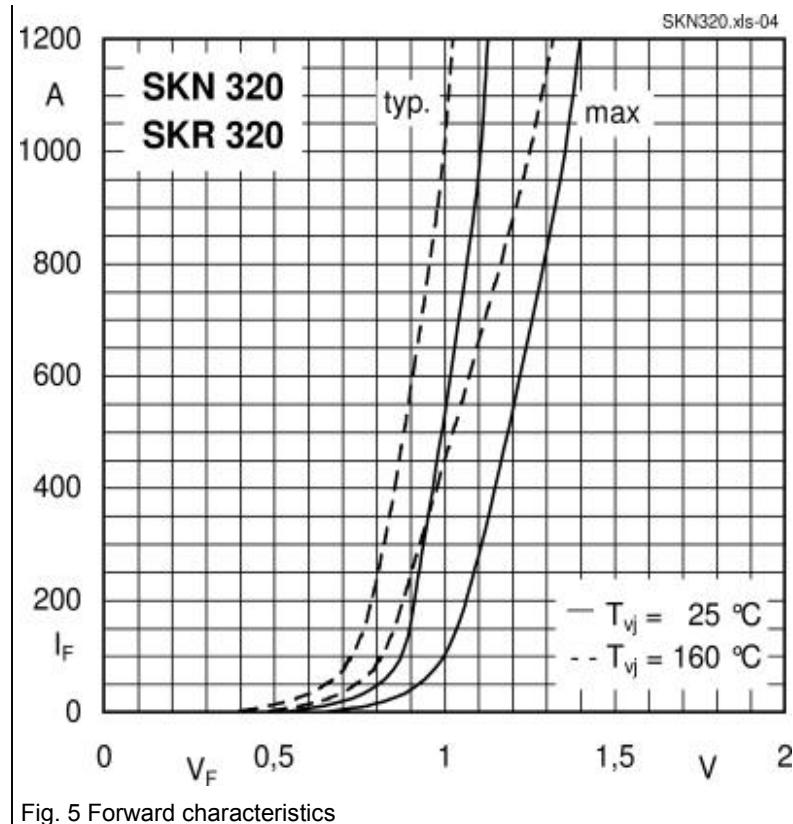


Fig. 5 Forward characteristics

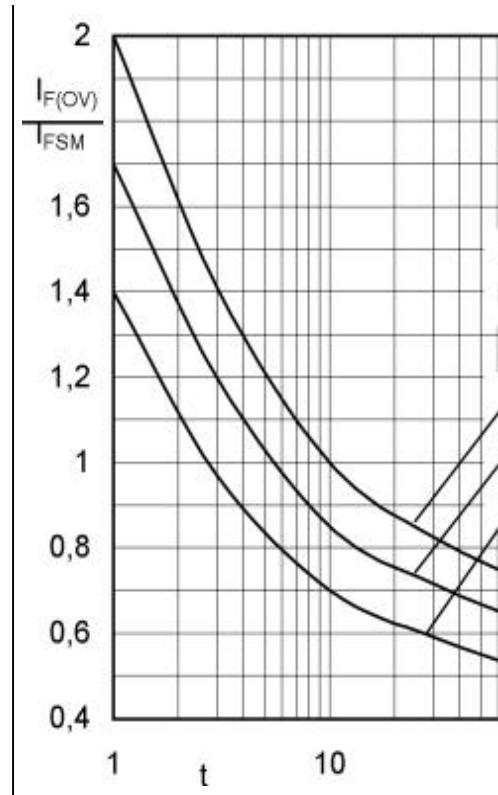
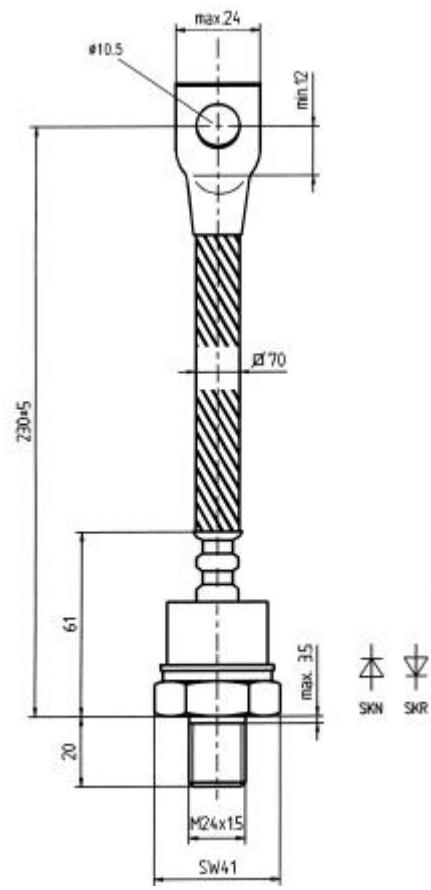


Fig. 6 Surge overload current vs. time

Cases / Circuits



Case E 16 (IEC 60191: A 22 B)
